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June 2014

FDB016N04AL7

N-Channel PowerTrench[®] MOSFET 40 V, 306 A, 1.6 m Ω

Features

- $R_{DS(on)}$ = 1.16 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 80 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{\mbox{\footnotesize{DS(on)}}}$
- · High Power and Current Handling Capability
- · RoHS Compliant

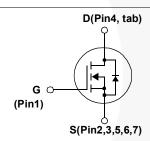
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advance PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- Motor drives and Uninterruptible Power Supplies





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter	FDB016N04AL7	Unit
V_{DSS}	Drain to Source Voltage		40	V
V _{GSS}	Gate to Source Voltage		±20	V
1		- Continuous (T _C = 25°C, Silicon Limited)	306*	
D	Drain Current	- Continuous (T _C = 100°C, Silicon Limited)	216*	Α
		- Continuous (T _C = 25°C, Package Limited)	160	
DM	Drain Current	- Pulsed (Note 1)	1224	Α
- AS	Single Pulsed Avalanche	Energy (Note 2)	1350	mJ
dv/dt	Peak Diode Recovery dv/d	dt (Note 3)	6.0	V/ns
n	Power Dissipation	(T _C = 25°C)	283	W
D	Power Dissipation	- Derate Above 25°C	1.89	W/°C
Γ _J , T _{STG}	Operating and Storage Te	mperature Range	-55 to +175	°C
Γ _L	Maximum Lead Temperat 1/8" from Case for 5 Seco		300	°C

^{*}Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 160 A.

1. Gate
2. Source
3. Source
4. Drain
5. Source
6. Source
7. Source

Thermal Characteristics

Symbol	Parameter FDB016N04AL7			
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.53	°C/W	
$R_{\theta JA}$	hermal Resistance, Junction to Ambient, Max. 62.5		C/VV	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDB016N04AL7	FDB016N04A	D2PAK-7L	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ} C$	40	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C	-	0.03	-	V/°C
	Zero Gate Voltage Drain Current	V _{DS} = 32 V, V _{GS} = 0 V	-	-	10	
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 32 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μΑ
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	1.0	-	3.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 80 A	-	1.16	1.6	mΩ
9 _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 80 A	-	381	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V = 25 V V = 0 V		-	8715	11600	pF
C _{oss}	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz		-	2035	2710	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 101112		-	230	-	pF
Q _{g(tot)}	Total Gate Charge at 10V			-	129	167	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DS} = 32 \text{ V}, I_{D} = 80 \text{ A},$		-	28	-	nC
Q _{gs2}	Gate Charge Threshold to Plateau	V _{GS} = 10 V		-	12	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	17	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	21	52	ns
t _r	Turn-On Rise Time	$V_{DD} = 20 \text{ V}, I_{D} = 80 \text{ A},$	-	14	38	ns
t _{d(off)}	Turn-Off Delay Time	$R_G = 4.7 \Omega, V_{GS} = 10 V$	-	118	246	ns
t _f	Turn-Off Fall Time	(Note 4)	- /	33	76	ns
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	-/	1.25	-	Ω

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Dio	Maximum Continuous Drain to Source Diode Forward Current		-	306	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	1224	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 80 A	-	-	1.3	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 80 A,	-	68	-	ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt = 100 A/μs	-	84	-	nC

Notes

1. Repetitive rating: pulse-width limited by maximum junction temperature.

^{2.} L = 3 mH, I_{AS} = 30 A, V_{DD} = 25 V, R_G = 25 Ω , starting T_J = 25°C.

^{3.} I $_{SD} \leq$ 80 A, di/dt \leq 200 A/µs, V $_{DD} \leq$ BV $_{DSS},$ starting T $_{J}$ = 25°C.

^{4.} Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

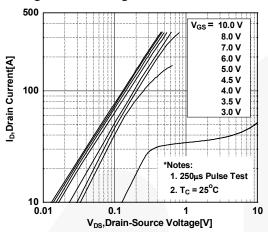


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

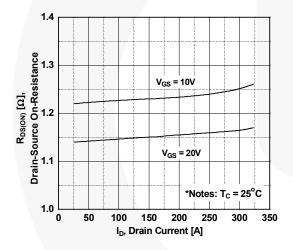


Figure 5. Capacitance Characteristics

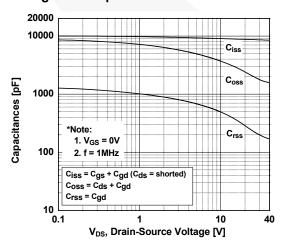


Figure 2. Transfer Characteristics

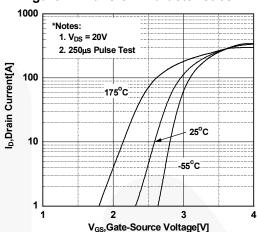


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

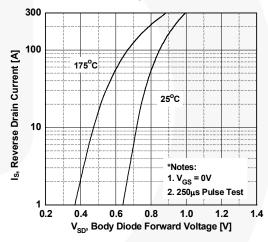
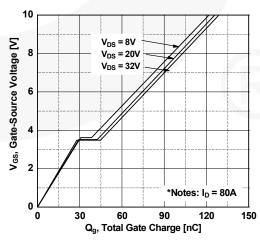


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

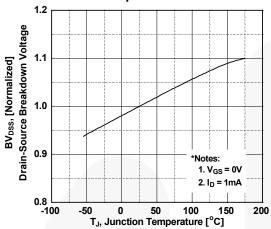


Figure 8. On-Resistance Variation vs. Temperature

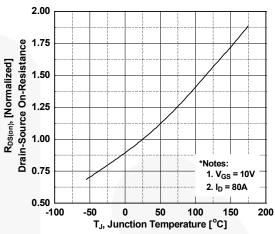


Figure 9. Maximum Safe Operating Area

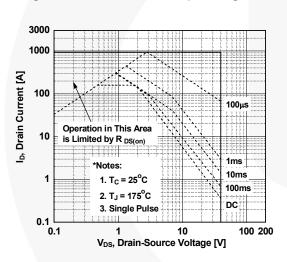


Figure 10. Maximum Drain Current vs.

Case Temperature

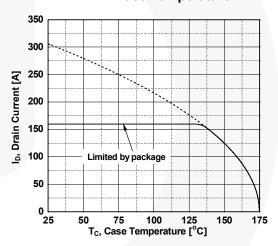
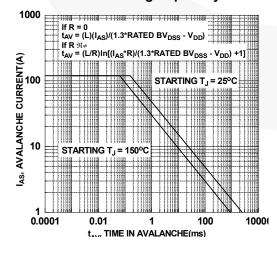


Figure 11. Unclamped Inductive Switching Capability



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve

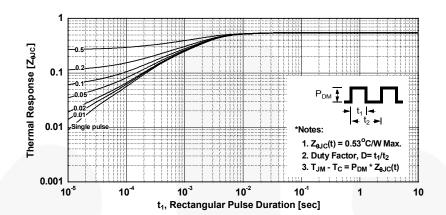


Figure 13. Gate Charge Test Circuit & Waveform

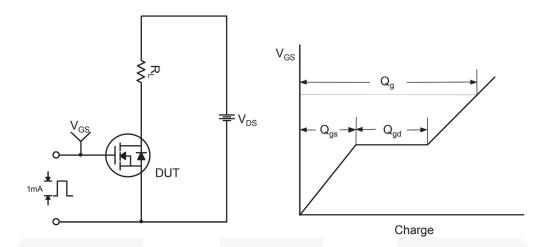


Figure 14. Resistive Switching Test Circuit & Waveforms

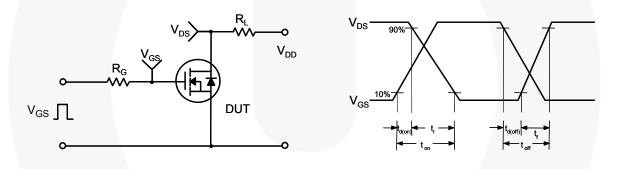
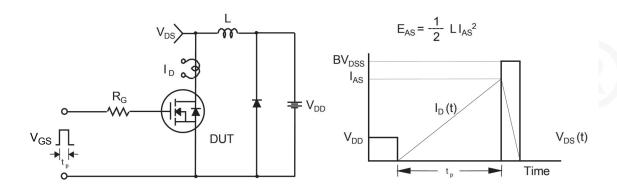
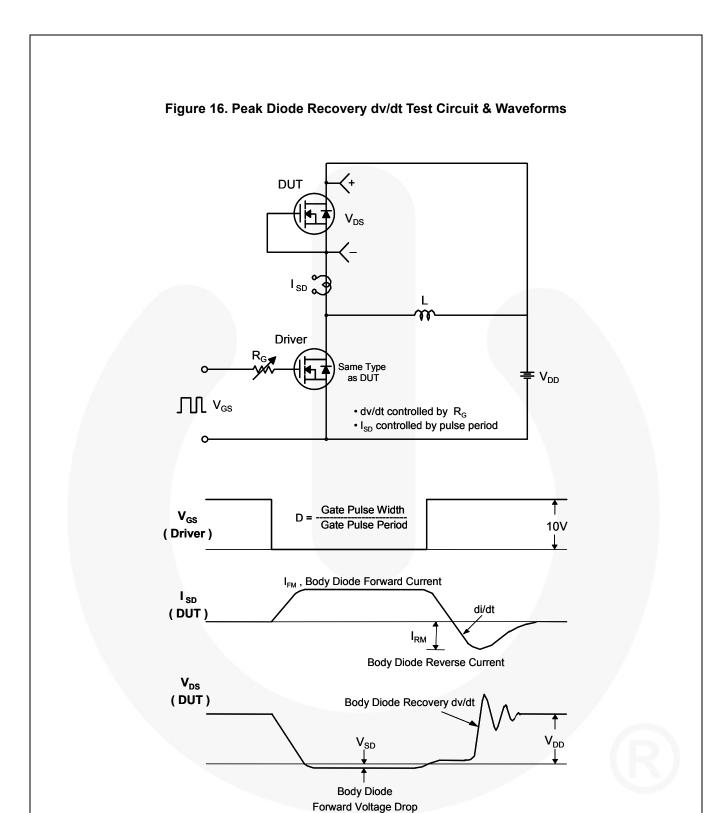


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms





Mechanical Dimensions

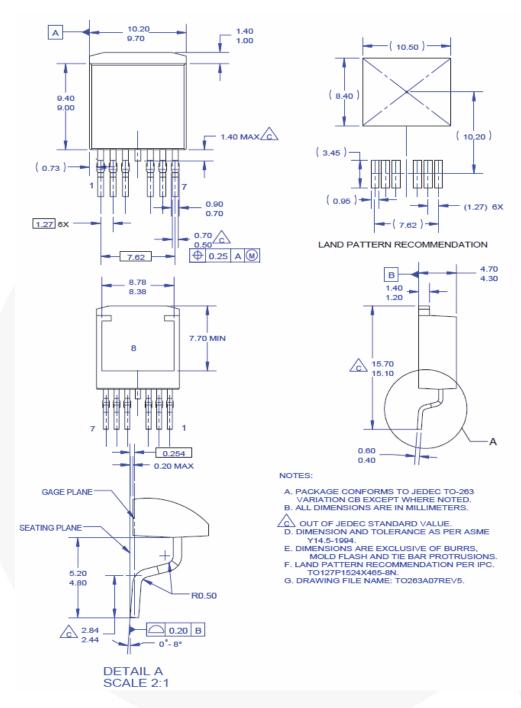


Figure 17. TO263 (D²PAK), Molded, 7-Lead, Surface Mount

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